IXYS

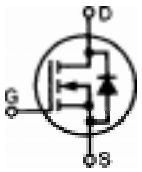
HiPerFET™ Power MOSFETs

IXFH/IXFM42N20
IXFH/IXFM/IXFT50N20
IXFH/IXFT58N20

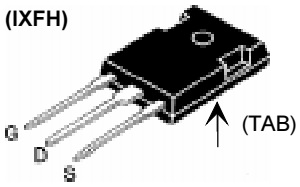
V_{DSS}	I_{D25}	$R_{DS(on)}$
200 V	42 A	60mΩ
200 V	50 A	45mΩ
200 V	58 A	40mΩ

$t_{rr} \leq$ 200 ns

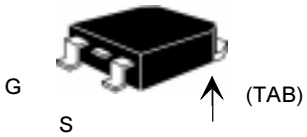
N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family



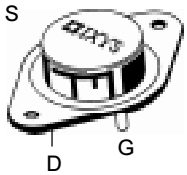
TO-247 AD (IXFH)



TO-268 (D3) Case Style



TO-204 AE (IXFM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		200	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		200	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C	42N20	42	A
		50N20	50	A
		58N20	58	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	42N20	168	A
		50N20	200	A
		58N20	232	A
I_{AR}	T_C = 25°C	42N20	42	A
		50N20	50	A
		58N20	58	A
E_{AR}	T_C = 25°C		30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \leq V_{DSS}$, $T_J \leq$ 150°C, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		300	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250 μA		200			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2		4	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±100	nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS}	T_J = 25°C			200	μA
	V_{GS} = 0 V	T_J = 125°C			1	mA

Features
- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

Applications
- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- High power surface mountable package
- High power density

IXYS

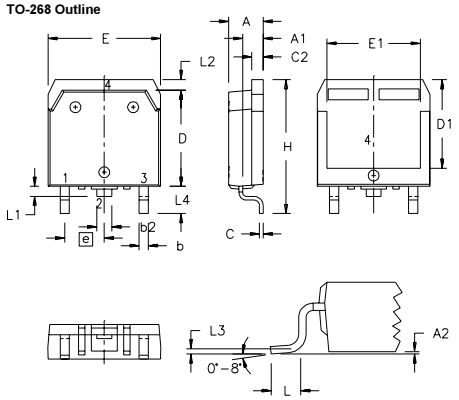
IXFH42N20 IXFM42N20 IXFH50N20 IXFM50N20 IXFT50N20 IXFH58N20 IXFM58N20 IXFT58N20

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25}	42N20			0.060	Ω
		50N20			0.045	Ω
		58N20			0.040	Ω
	Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %					
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test		20	32		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz			4400		pF
C_{oss}				800		pF
C_{rss}				285		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}			18	25	ns
t_r	R_G = 1 Ω (External)			15	20	ns
$t_{d(off)}$				72	90	ns
t_f				16	25	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}			190	220	nC
Q_{gs}				35	50	nC
Q_{gd}				95	110	nC
R_{thJC}					0.42	K/W
R_{thCK}	(TO-247 and TO-204 Case styles)			0.25		K/W

Source-Drain Diode

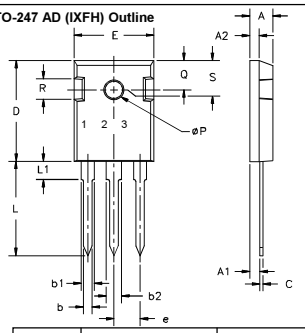
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0 V	42N20			42	A
		50N20			50	A
		58N20			58	A
I_{SM}	Repetitive;	42N20			168	A
	pulse width limited by T_{JM}	50N20			200	A
		58N20			232	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %				1.5	V
t_{rr}	I_F = 25A, -di/dt = 100 A/μs, V_R = 100 V	T_J = 25°C			200	ns
		T_J = 125°C			300	ns
Q_{RM}		T_J = 25°C		1.5		μC
		T_J = 125°C		2.6		μC
I_{RM}		T_J = 25°C		19		A
		T_J = 125°C		23		A

TO-268 Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

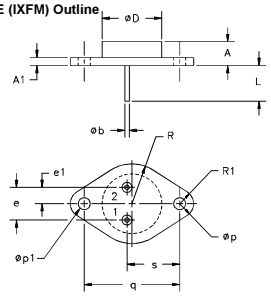
TO-247 AD (IXFH) Outline



Terminals:
1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

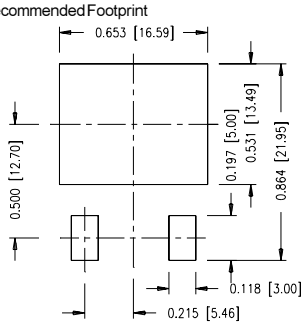
TO-204 AE (IXFM) Outline



Pins: 1 - Gate, 2 - Source, Case - Drain

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	6.4	11.4	.250	.450
A1	1.53	3.42	.060	.135
Øb	1.45	1.60	.057	.063
ØD		22.22		.875
e	10.67	11.17	.420	.440
e1	5.21	5.71	.205	.225
L	11.18	12.19	.440	.480
Øp	3.84	4.19	.151	.165
Øp1	3.84	4.19	.151	.165
q	30.15 BSC		1.187 BSC	
R	12.58	13.33	.495	.525
R1	3.33	4.77	.131	.188
s	16.64	17.14	.655	.675

Min Recommended Footprint



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig. 1 Output Characteristics

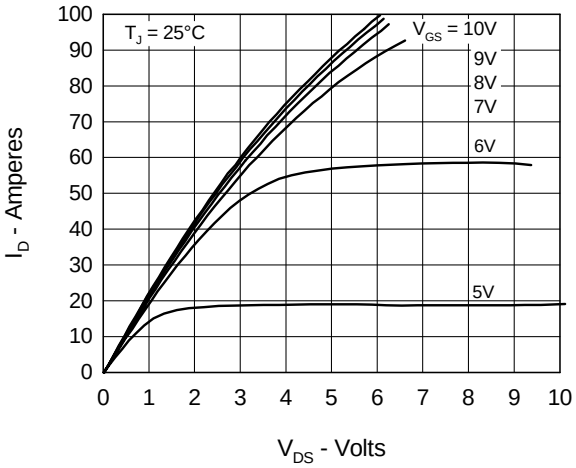


Fig. 2 Input Admittance

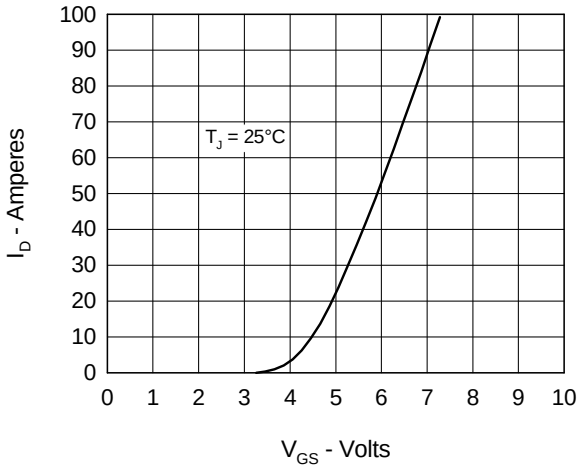


Fig. 3 $R_{DS(on)}$ vs. Drain Current

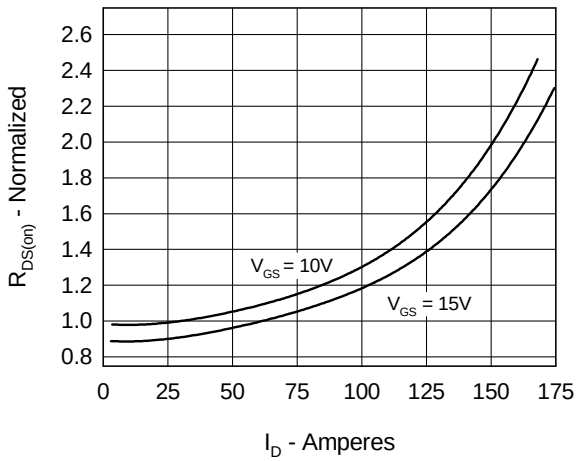


Fig. 4 Temperature Dependence of Drain to Source Resistance

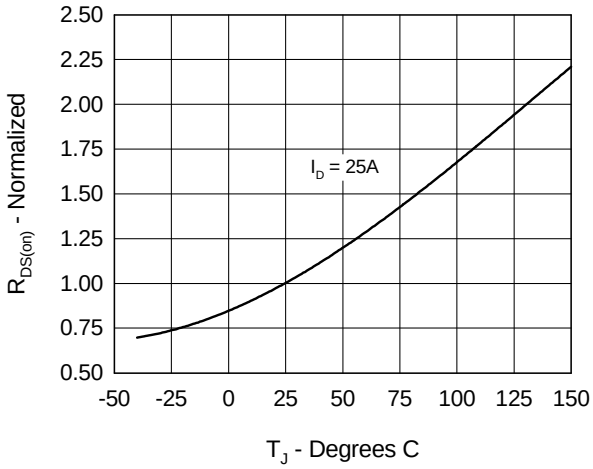


Fig. 5 Drain Current vs. Case Temperature

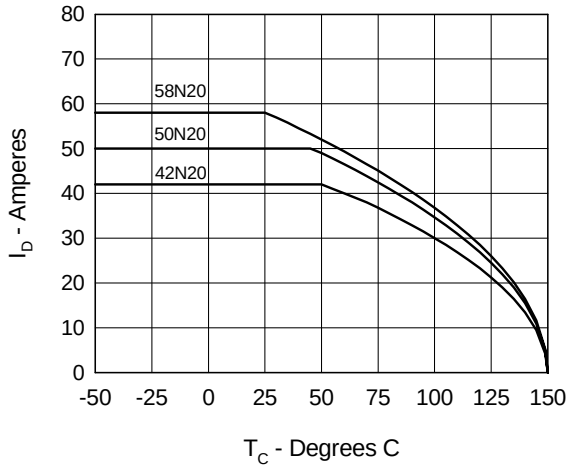


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

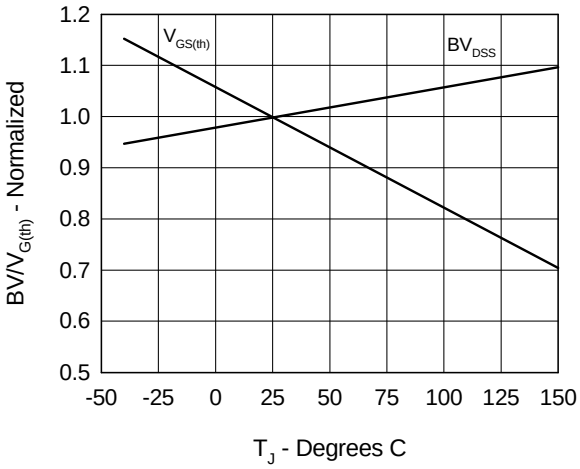


Fig.7 Gate Charge Characteristic Curve

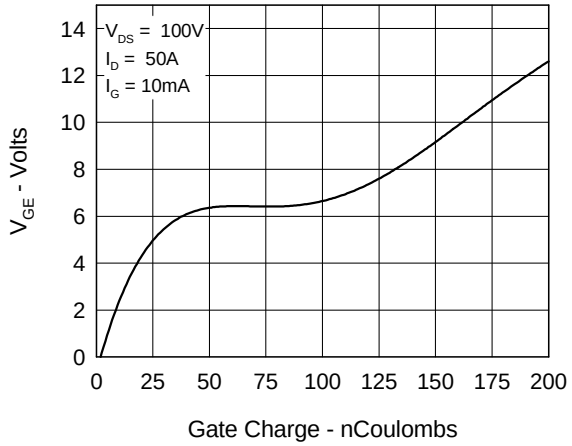


Fig.8 Forward Bias Safe Operating Area

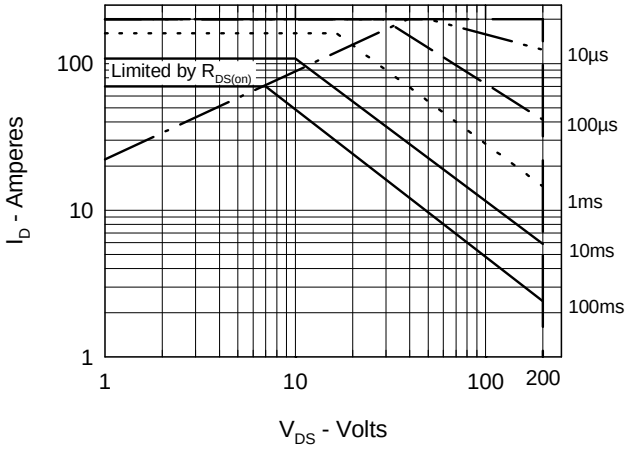


Fig.9 Capacitance Curves

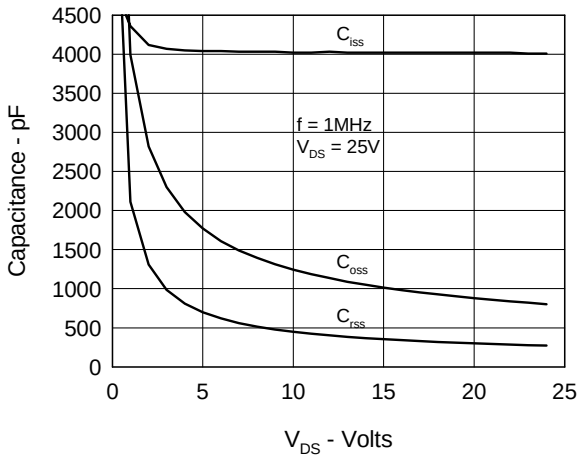


Fig.10 Source Current vs. Source to Drain Voltage

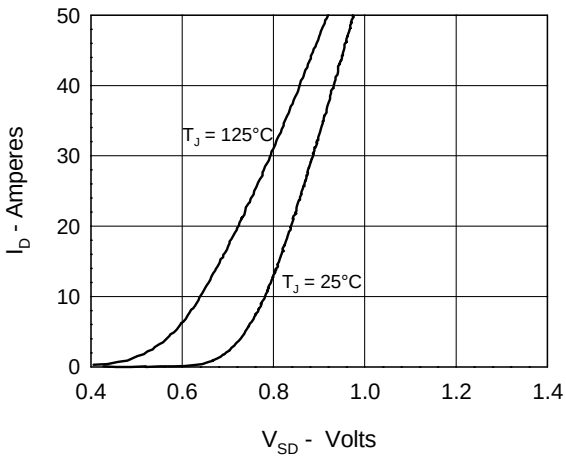


Fig.11 Transient Thermal Impedance